

09/844958

IR-2084 (2-2637)

TRENCH MOS DEVICE AND PROCESS FOR RADHARD DEVICE

ABSTRACT OF THE DISCLOSURE

A MOSgated device is resistant to both high radiation and SEE environments. The active area of the device is formed of trench devices having a thin gate dielectric on the trench walls and a thicker dielectric on the trench bottoms over the device depletion region. Termination rings formed of ring-shaped trenches containing floating polysilicon plugs surrounds and terminates the device active area.